TOSHIBA Field-Effect Transistor Silicon P-Channel MOS Type

# SSM6J205FE

High-Speed Switching Applications
Power Management Switch Applications

• 1.8V drive

P-ch 2-in-1

• Low ON-resistance:  $R_{on} = 460 \text{ m}\Omega \text{ (max) } (@V_{GS} = -1.8 \text{ V})$ 

 $R_{on} = 306 \text{ m}\Omega \text{ (max) (@V_{GS} = -2.5 V)}$ 

 $R_{on} = 234 \text{ m}\Omega \text{ (max) } (@V_{GS} = -4.0 \text{ V})$ 

# Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Drain-source voltage		$V_{DS}$	-20	V	
Gate-source voltage		V <sub>GSS</sub>	± 8	V	
Drain current	DC	I <sub>D</sub>	-0.8	Α	
	Pulse	I <sub>DP</sub>	-1.6		
Drain power dissipation		P <sub>D</sub> (Note 1)	500	mW	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	

Note:

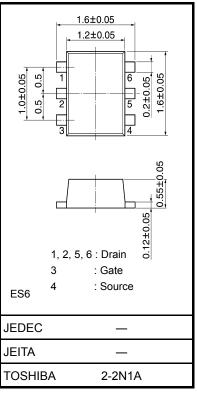
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual

reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on an FR4 board (total dissipation) (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

## Unit: mm



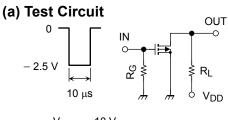
Weight: 3 mg (typ.)

## **Electrical Characteristics (Ta = 25°C)**

Charact	teristic	Symbol	Test Conditions	Min	Тур.	Max	Unit
Drain-source breakdown voltage		V (BR) DSS	$I_D = -1 \text{ mA}, V_{GS} = 0$	- 20	_	_	V
		V (BR) DSX	$I_D = -1 \text{ mA}, V_{GS} = +8 \text{ V}$	- 12		_	
Drain cutoff current	1	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0$	_	_	- 10	μА
Gate leakage curre	nt	I <sub>GSS</sub>	$V_{GS}=\pm \ 8 \ V, \ V_{DS}=0$	_	_	± 1	μА
Gate threshold volt	age	V <sub>th</sub>	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$	- 0.3	_	- 1.0	V
Forward transfer ad	dmittance	Y <sub>fs</sub>	$V_{DS} = -3 \text{ V}, I_D = -0.6 \text{ A}$ (Note 2)	1.5	2.5	_	S
Drain-source ON-resistance		R <sub>DS</sub> (ON)	$I_D = -0.6 \text{ A}, V_{GS} = -4.0 \text{ V}$ (Note 2)	_	175	234	mΩ
			$I_D = -0.4 \text{ A}, V_{GS} = -2.5 \text{ V}$ (Note 2)	_	230	306	
			$I_D = -0.1 \text{ A}, V_{GS} = -1.8 \text{ V}$ (Note 2)	_	300	460	
Input capacitance		C <sub>iss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	250	_	pF
Output capacitance	acitance $C_{OSS}$ $V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		_	45	_	pF	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = 0, f = 1 MHz	_	35		pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = -10 \text{ V}, I_D = -0.25 \text{ A},$	_	12	_	ns
	Turn-off time	t <sub>off</sub>	$V_{GS} = 0$ to $-2.5$ V, $R_G = 4.7$ $\Omega$	_	18	_	
Drain-source forward voltage		V <sub>DSF</sub>	$I_D = 0.8 \text{ A}, V_{GS} = 0 \text{ V}$ (Note 2)	_	0.85	1.2	V

Note 2: Pulse test

## **Switching Time Test Circuit**



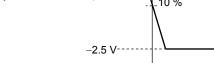
 $V_{DD} = -10 \text{ V}$  $R_G = 4.7 \Omega$ 

 $D.U. \leqq 1~\%$ 

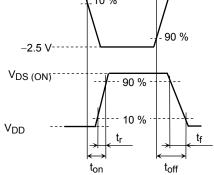
 $V_{IN}\text{: }t_{r}\text{, }t_{f}<5\text{ ns}$ Common Source

Ta = 25 °C

#### (b) V<sub>IN</sub>

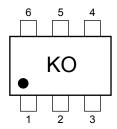


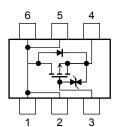
(c) Vout



## Marking

## **Equivalent Circuit (top view)**





#### **Precaution**

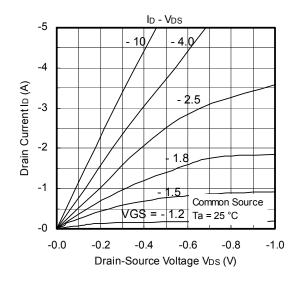
 $V_{th}$  can be expressed as the voltage between gate and source when the low operating current value is  $I_D = -1$  mA for this product. For normal switching operation, V<sub>GS (on)</sub> requires a higher voltage than V<sub>th</sub>, and V<sub>GS (off)</sub> requires a lower voltage than V<sub>th.</sub>

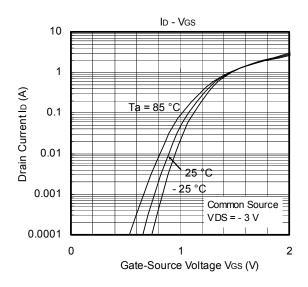
(The relationship can be established as follows:  $V_{GS (off)} < V_{th} < V_{GS (on)}$ .)

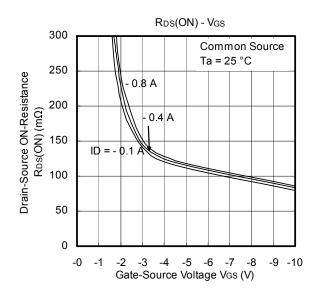
Take this into consideration when using the device.

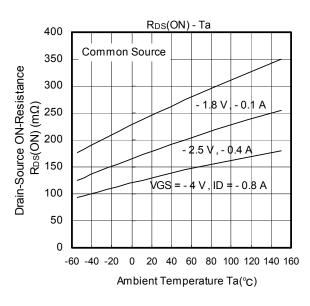
#### **Handling Precaution**

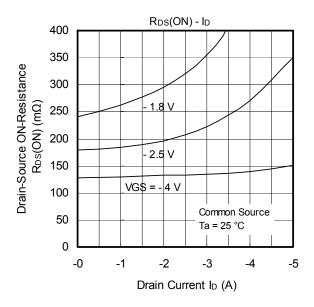
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

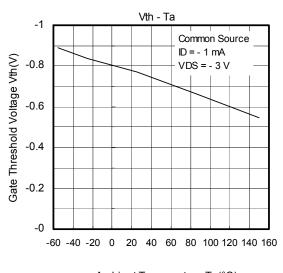




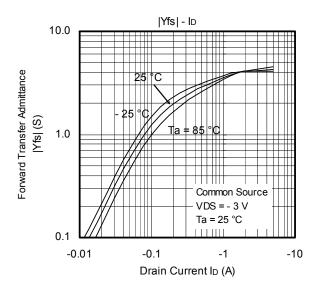


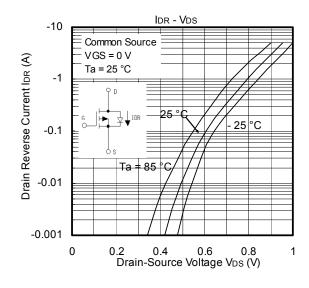


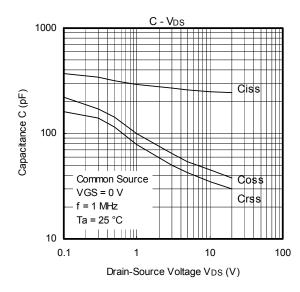


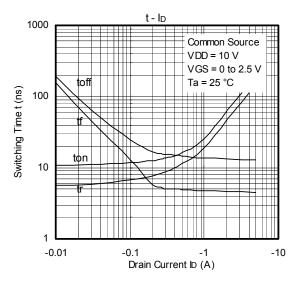


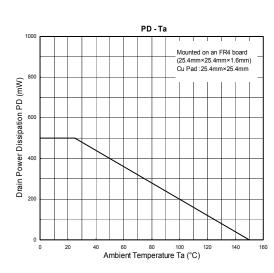
Ambient Temperature  $Ta(^{\circ}C)$ 











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20070701-EN GENERAL

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